



# 75 VOLT 20 AMP MOSFET H-BRIDGE WITH GATE DRIVE

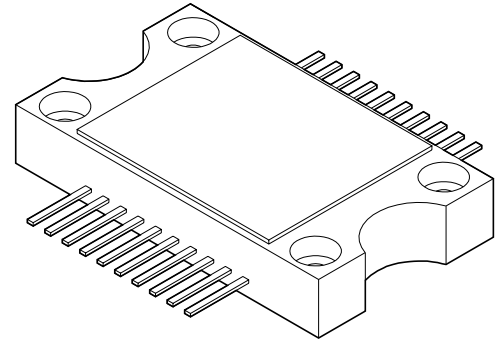
# 4226

4707 Dey Road Liverpool, N.Y. 13088

(315) 701-6751

### FEATURES:

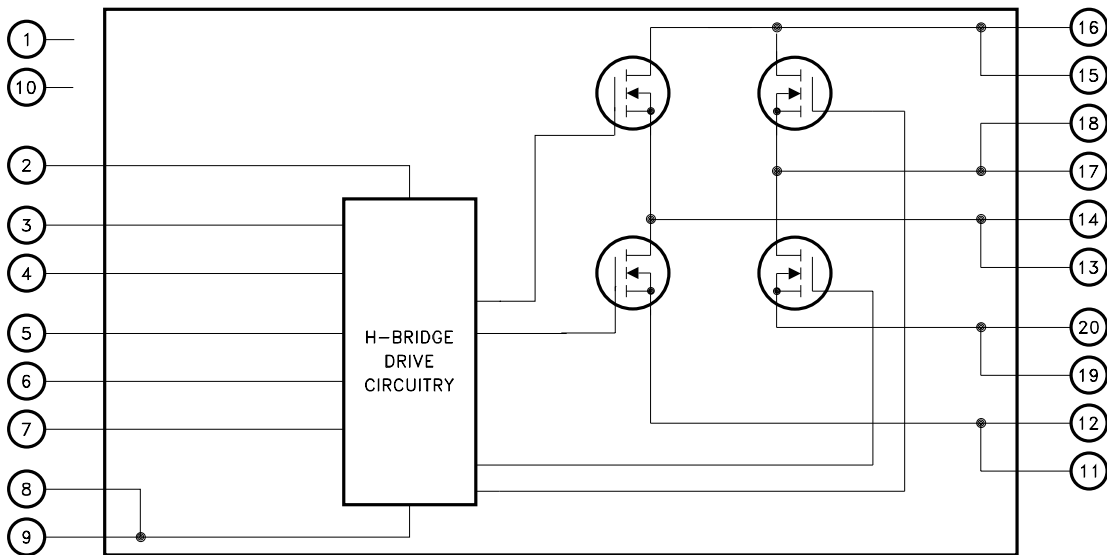
- Low RDS(ON) 0.013Ω Typical
- Low Cost Complete H-Bridge
- 20 Amp Capability, 75 Volt Maximum Rating
- Self-contained Smart Lowside/Highside Drive Circuitry
- Shoot-through Protection
- Isolated Case Allows Direct Heatsinking
- Logic Level Disable Input
- Individual Logic Level Gate Drive Inputs for Various Modulation Schemes



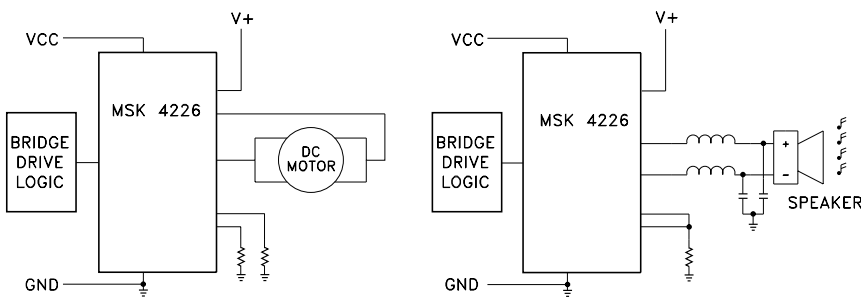
### DESCRIPTION:

The MSK 4226 is a complete H-Bridge circuit to be used for DC brushed motor control or Class D switchmode amplification. All of the drive/control circuitry for the lowside and highside switches are internal to the circuit. Logic level inputs are provided for controlling each MOSFET independently, allowing every possible switch combination except those that would cause a simultaneous conduction or shoot-through condition for each half bridge. This gives the user freedom to use various modulation schemes for PWM control. The MSK 4226 is constructed in a space efficient plastic power package that can be directly bolted to a heatsink.

### EQUIVALENT SCHEMATIC



### TYPICAL APPLICATIONS



### PIN-OUT INFORMATION

1	NC	20	RSENSE A
2	VCC	19	RSENSE A
3	BHI	18	OUTPUT A
4	DIS	17	OUTPUT A
5	BLI	16	V+
6	AHI	15	V+
7	ALI	14	OUTPUT B
8	GND	13	OUTPUT B
9	GND	12	RSENSE B
10	NC	11	RSENSE B

## ABSOLUTE MAXIMUM RATINGS <sup>⑤</sup>

V <sub>+</sub> High Voltage Supply . . . . .	75V	T <sub>ST</sub> Storage Temperature Range . . . . .	-55° C to + 125° C
V <sub>CC</sub> Logic Supply . . . . .	16V	T <sub>LD</sub> Lead Temperature Range . . . . .	300° C (10 Seconds)
I <sub>OUT</sub> Continuous Output Current . . . . .	20A	T <sub>C</sub> Case Operating Temperature MSK4226 . . . . .	-40° C to + 85° C
I <sub>PK</sub> Peak Output Current . . . . .	40A	T <sub>J</sub> Junction Temperature . . . . .	+ 150° C
V <sub>OUT</sub> Output Voltage Range . . . . .	GND -2V min. to V <sub>+</sub> max.		
θ <sub>JC</sub> Thermal Resistance . . . . .	3.0° C/W (Output Switches @ 125° C)		

## ELECTRICAL SPECIFICATIONS

T<sub>c</sub> = + 25° C Unless Otherwise Specified

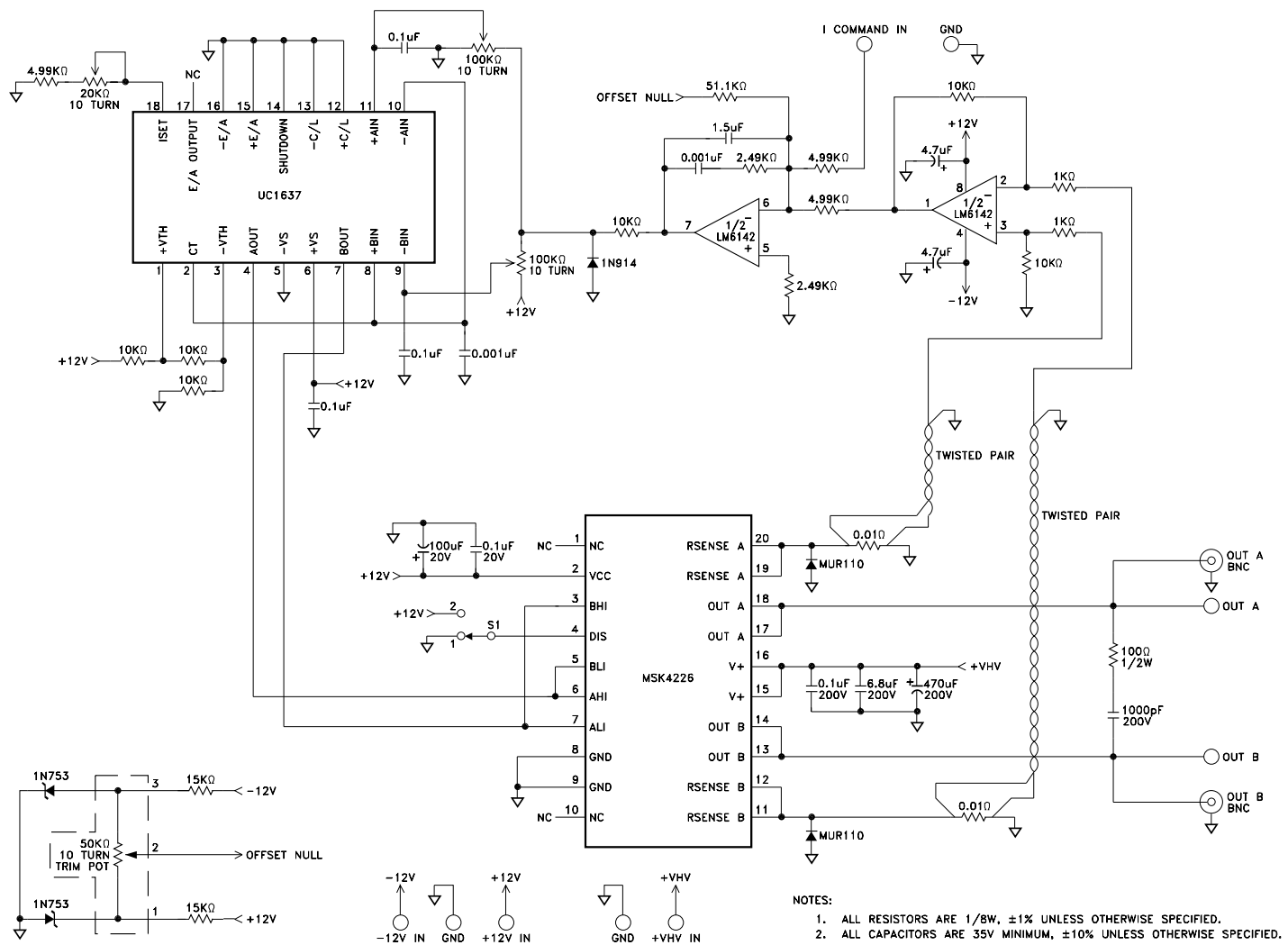
Parameter	Test Conditions <sup>②</sup>	MSK 4226			Units
		Min.	Typ.	Max.	
<b>OUTPUT CHARACTERISTICS</b>					
R <sub>DS (ON)</sub> <sup>① ④</sup>	Each MOSFET I <sub>D</sub> = 20A	-	-	0.013	Ω
V <sub>DS(ON)</sub> Voltage	Each MOSFET I <sub>D</sub> = 20A <sup>③</sup>	-	0.45	0.52	V
Instantaneous Forward Voltage	Each MOSFET I <sub>S</sub> = 20A Intrinsic Diode <sup>③</sup>	-	1.0	1.3	V
Reverse Recovery Time <sup>①</sup>	Intrinsic Diode	-	-	280	nS
Leakage Current	Each MOSFET V <sub>+</sub> = 70V	-	10	250	uA
<b>V<sub>CC</sub> SUPPLY CHARACTERISTICS</b>					
Quiescent Bias Current		-	29	50	mA
V <sub>CC</sub> Voltage Range <sup>①</sup>		10	12	15	V
<b>LOGIC CONTROL INPUTS, ALI, BLI, AHI, BHI and DIS <sup>①</sup></b>					
Input Voltage LO		-	-	0.8	V
Input Voltage HI		2.7	-	-	V
Input Current (V <sub>IN</sub> = 0V)		-	-	270	uA
<b>SWITCHING CHARACTERISTICS <sup>①</sup> R<sub>L</sub> = 100Ω</b>					
Rise Time		-	40	-	nS
Fall Time		-	30	-	nS
Dead Time		-	45	-	nS

### NOTES:

- ① Guaranteed by design but not tested. Typical parameters are representative of actual device performance but are for reference only.
- ② V<sub>CC</sub> = + 12V, V<sub>+</sub> = 28V, R<sub>SENSE</sub> A,B = Ground, DIS = 0V unless otherwise specified.
- ③ Measured using a 300μS pulse with a 2% Duty Cycle.
- ④ On Resistance is specified for the Internal MOSFET for Thermal Calculations. It does not include the package pin resistance.
- ⑤ Continuous operation at or above absolute maximum ratings may adversely effect the device performance and/or life cycle.



# MSK4226 EVALUATION SCHEMATIC



- NOTES:
1. ALL RESISTORS ARE 1/8W, ±1% UNLESS OTHERWISE SPECIFIED.
  2. ALL CAPACITORS ARE 35V MINIMUM, ±10% UNLESS OTHERWISE SPECIFIED.

